Elektronische Bauelemente

SSE35P10-C

-35A, -100V, $R_{DS(ON)}$ 50mΩ

P-Channel Enhancement Mode Power MOSFET

RoHS Compliant Product

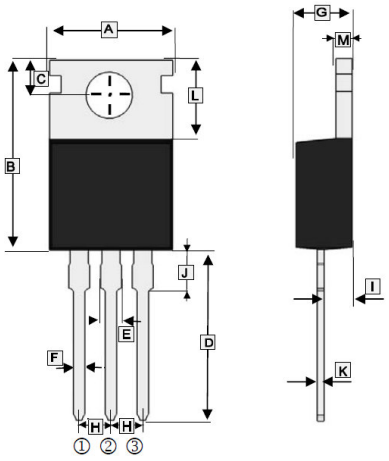
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

The SSE35P10-C is the highest performance trench P-Ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The SSE35P10-C meet the RoHS and Green Product requirement with full function reliability approved.

TO-220

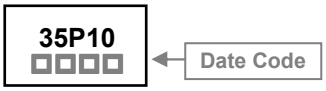


REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	9.70	10.60	H	2.54 TYP.	
B	14.22	16.5	I	2.03	2.92
C	2.54.	3.40	J	2.70	3.30
D	12.7	14.7	K	0.33	0.65
E	1.17	1.78	L	5.5	7
F	0.4	1.00	M	1.20	1.40
G	3.60	4.82			

FEATURES

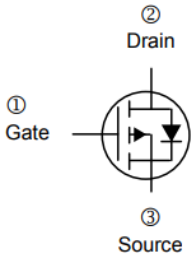
- Advanced High Cell Density Trench Technology
- Super Low Gate Charge

MARKING



ORDER INFORMATION

Part Number	Type
SSE35P10-C	Lead (Pb)-free and Halogen-free



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	-100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [1], @V_{GS}= -10V	T_C=25°C	I_D	-35	A
	T_C=100°C		-23	
Pulsed Drain Current [3]		I_{DM}	-100	A
Total Power Dissipation [2]	T_C=25°C	P_D	104	W
Operating Junction & Storage Temperature		T_J, T_{STG}	-55~150	°C
Thermal Resistance Ratings				
Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	1.2	°C/W
Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	62	

ELECTRICAL CHARACTERISTICS (T_J=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV_{DSS}	-100	-	-	V	V_{GS}=0, I_D= -250uA
Gate Threshold Voltage	$V_{GS(th)}$	-1	-	-2.5	V	V_{DS}=V_{GS}, I_D= -250uA
Forward Transconductance	g_{fs}	-	32	-	S	V_{DS}= -10V, I_D= -10A
Gate-Source Leakage Current	I_{GSS}	-	-	±100	nA	V_{GS}=±20V
Drain-Source Leakage Current	I_{DSS}	-	-	-1	uA	V_{DS}= -80V, V_{GS}=0
Static Drain-Source On-Resistance [3]	$R_{DS(ON)}$	-	-	50	mΩ	V_{GS}= -10V, I_D= -10A
		-	-	60		V_{GS}= -4.5V, I_D= -8A
Total Gate Charge	Q_g	-	92	-	nC	I_D= -14A V_{DS}= -80V V_{GS}= -10V
Gate-Source Charge	Q_{gs}	-	17.5	-		
Gate-Drain Change	Q_{gd}	-	14	-		
Turn-on Delay Time	$T_{d(on)}$	-	20.5	-	nS	V_{DD}= -50V I_D= -14A V_{GS}= -10V R_G=3.3Ω
Rise Time	T_r	-	32.2	-		
Turn-off Delay Time	$T_{d(off)}$	-	123	-		
Fall Time	T_f	-	63.7	-		
Input Capacitance	C_{iss}	-	6516	-	pF	V_{GS}=0 V_{DS}= -25V f=1MHz
Output Capacitance	C_{oss}	-	223	-		
Reverse Transfer Capacitance	C_{rss}	-	125	-		
Source-Drain Diode						
Diode Forward Voltage [3]	V_{SD}	-	-	-1.2	V	I_S= -1A, V_{GS}=0
Continuous Source Current [1]	I_S	-	-	-35	A	
Reverse Recovery Time	t_{rr}	-	31.2	-	nS	I_F= -14A, dI/dt=100A/μs, T_J=25°C
Reverse Recovery Charge	Q_{rr}	-	31.97	-	nC	

Notes:
1. Surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2. Pulse width limited by maximum junction temperature.
3. The data tested by pulsed, pulse width≦300μs, duty cycle≦2%.

CHARACTERISTIC CURVES

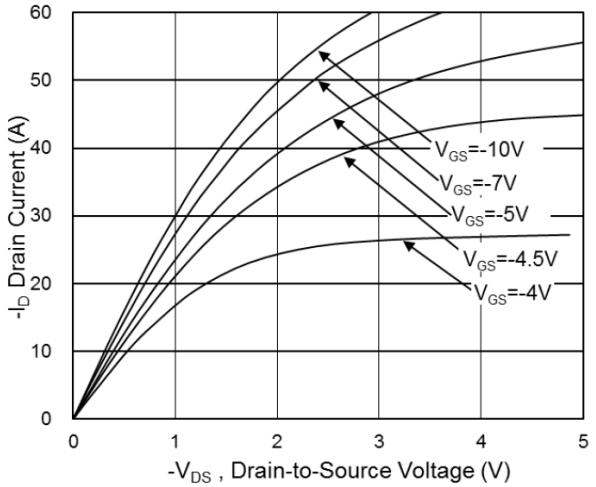


Fig.1 Typical Output Characteristics

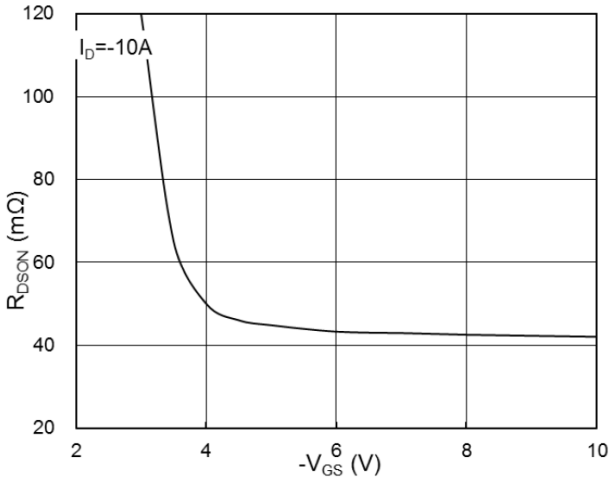


Fig.2 On-Resistance vs. G-S Voltage

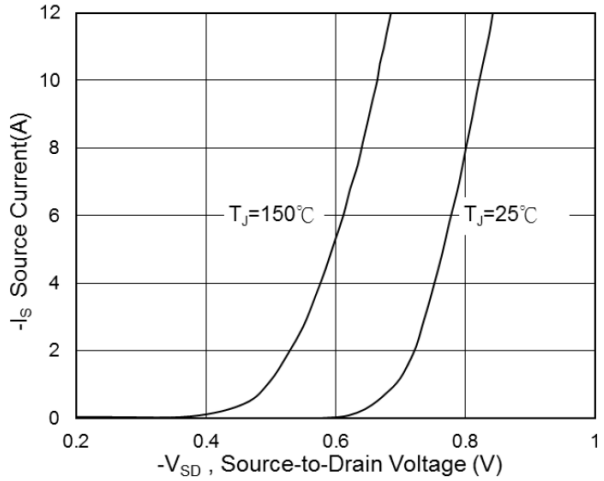


Fig.3 Typical S-D Diode Forward Voltage

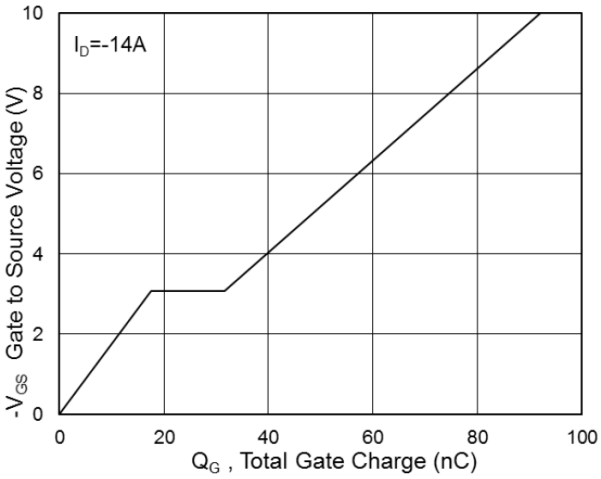


Fig.4 Gate-Charge Characteristics

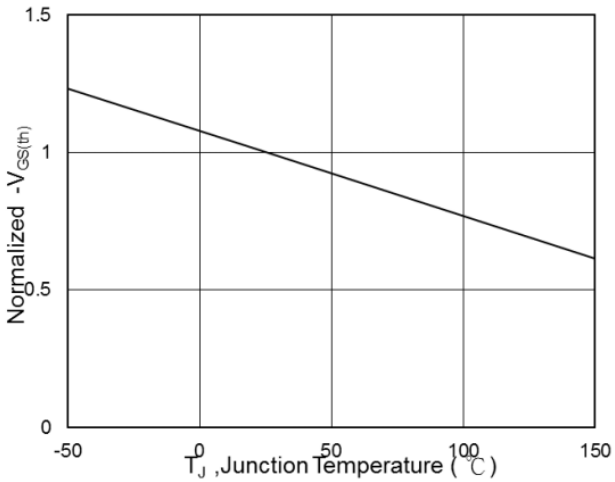


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

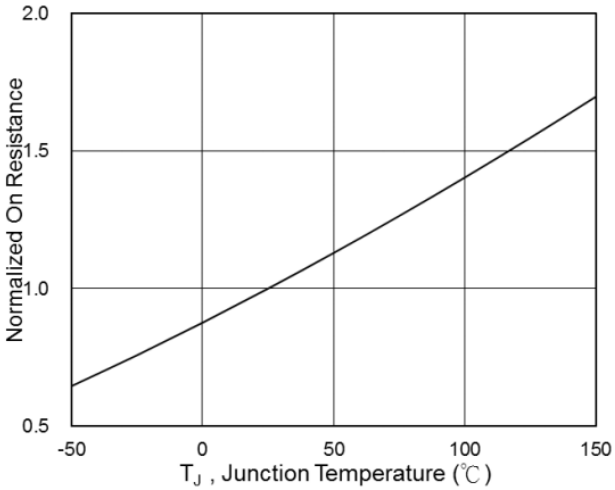


Fig.6 Normalized R_{DSON} vs. T_J

CHARACTERISTIC CURVES

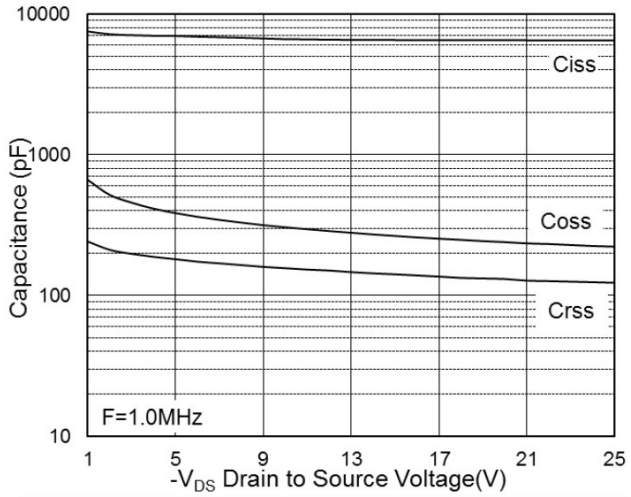


Fig.7 Capacitance

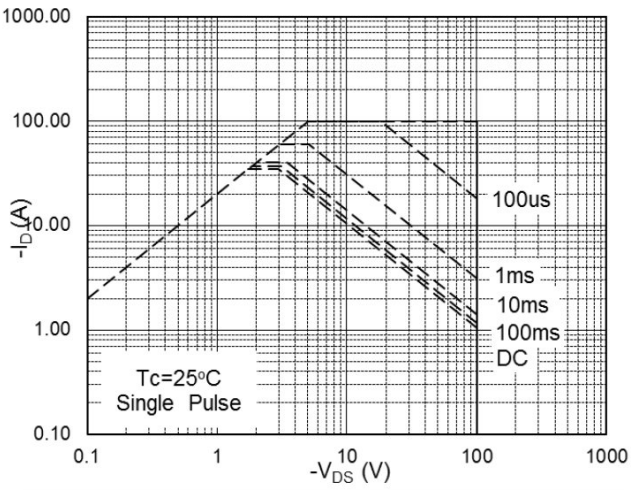


Fig.8 Safe Operating Area

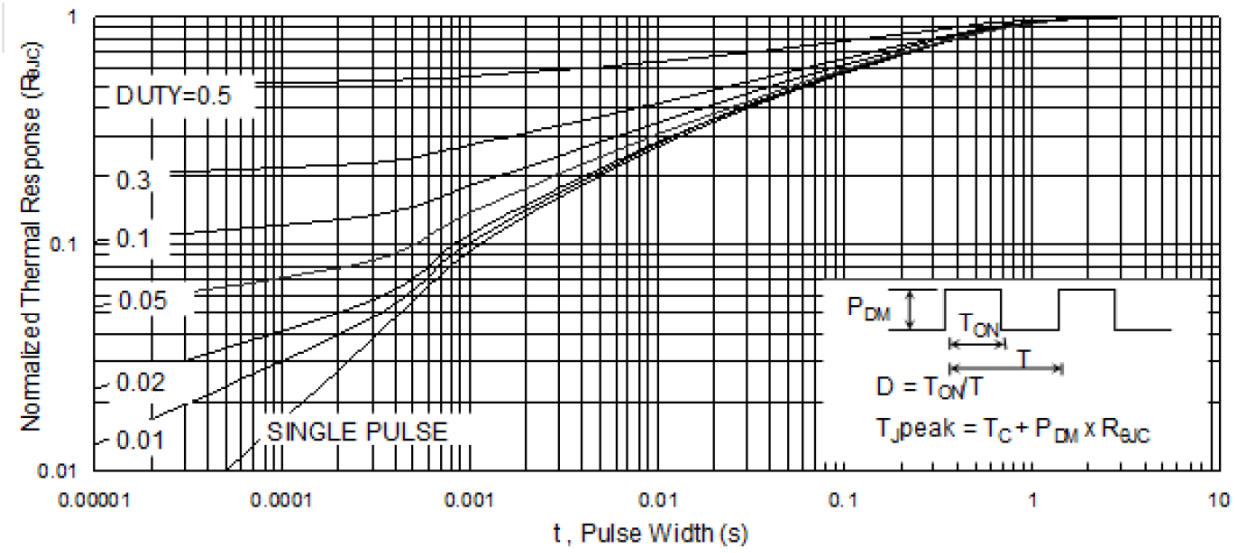


Fig.9 Normalized Maximum Transient Thermal Impedance

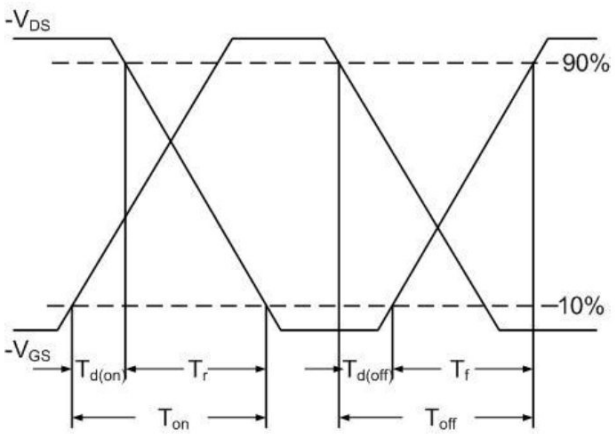


Fig.10 Switching Time Waveform

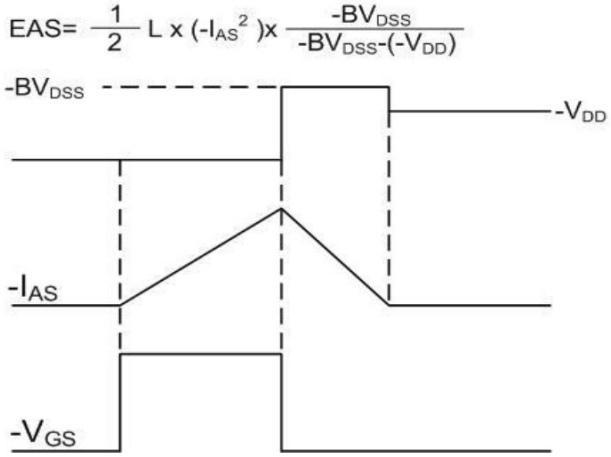


Fig.11 Unclamped Inductive Waveform